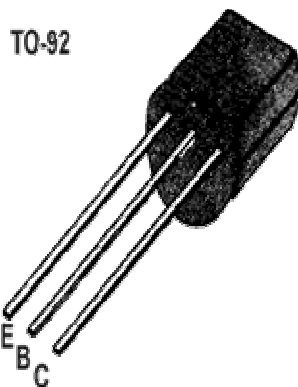


■■ **APPLICATION:** High Voltage Applications.

■■ **MAXIMUM RATINGS** (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	350	V
Collector-emitter voltage	V _{CEO}	350	V
Emitter-base voltage	V _{EBO}	6	V
Collector current	I _C	500	mA
Collector Power Dissipation	P _C	625	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55~150	°C



■■ **ELECTRICAL CHARACTERISTICS** (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE}	40				V _{CE} = 10V, I _C = 10mA
Collector Cut-off Current	I _{CBO}			0.1	μA	V _{CB} = 200V, I _E =0
Emitter Cut-off Current	I _{EBO}			0.1	μA	V _{EB} = 6V, I _C =0
Collector-Base Breakdown Voltage	BV _{CBO}	350			V	I _C = 0.1mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	350			V	I _C = 1mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	6			V	I _E = 0.1mA, I _C =0
Collector-Emitter Saturation Voltage	V _{CE(sat)}			0.5	V	I _C = 20mA, I _B = 2mA
Base-Emitter Saturation Voltage	V _{BE(sat)}			0.9	V	I _C = 20mA, I _B = 2mA
Gain bandwidth product	f _T	40			MHz	I _C = 10mA, V _{CE} = 20V
Common Base Output Capacitance	C _{ob}			6	PF	V _{CB} = 20V, I _E =0, f = 1MHz

■■ **h_{FE} Classification And Marking**

Classification

h_{FE}

>40